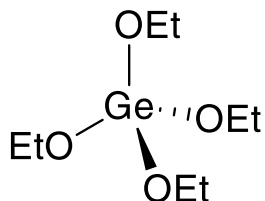


Catalog # 93-3206 Germanium(IV) ethoxide (99.99+%-Ge) PURATREM



Thermal Behavior:

- Melting point: -81°C
- Boiling point: 185.5°C
- Vapor Pressure: 0.885 Torr/40°C [1]

Technical Notes:

1. Used for germanium thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
GeTe _x	ALD	40°C	3.0 Torr	[Me ₃ Si] ₂ Te	50-120°C	1
GeSb _x Se _y Te _z	ALD	40°C	3.0 Torr	Sb(OEt) ₃ , (Me ₃ Si) ₂ Te, (Me ₃ Si) ₂ Se	70°C	2
GeTe _x S _{1-x}	PE-ALD	-	1.2 Torr	(Me ₃ Si) ₂ Te, H ₂ S	70°C	3

References:

1. [Chem. Mater. 2014, 26, 1583.](#)
2. [J. Mater. Chem. C, 2018, 6, 5025.](#)
3. [J. Mater. Chem. C, 2022, 10, 16803.](#)